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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100pjdfb-50

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	—	—	—	R5F100AG	R5F100BG	R5F100CG
	—		—	—	—	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	—	—	—	R5F100AF	R5F100BF	R5F100CF
	—		—	—	—	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	—		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	—		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	—		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	—		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	—	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	—		—	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	—	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	—		—	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	—	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	—		—	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	—		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	—
	—		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	—
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	—
	—		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	—
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	—	—	—
	—		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	—	—	—
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	—	—	—
	—		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	—	—	—
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	—	—	—
	—		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	—	—	—
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	—	—	—	—	—
	—		R5F101EA	R5F101FA	R5F101GA	—	—	—	—	—

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

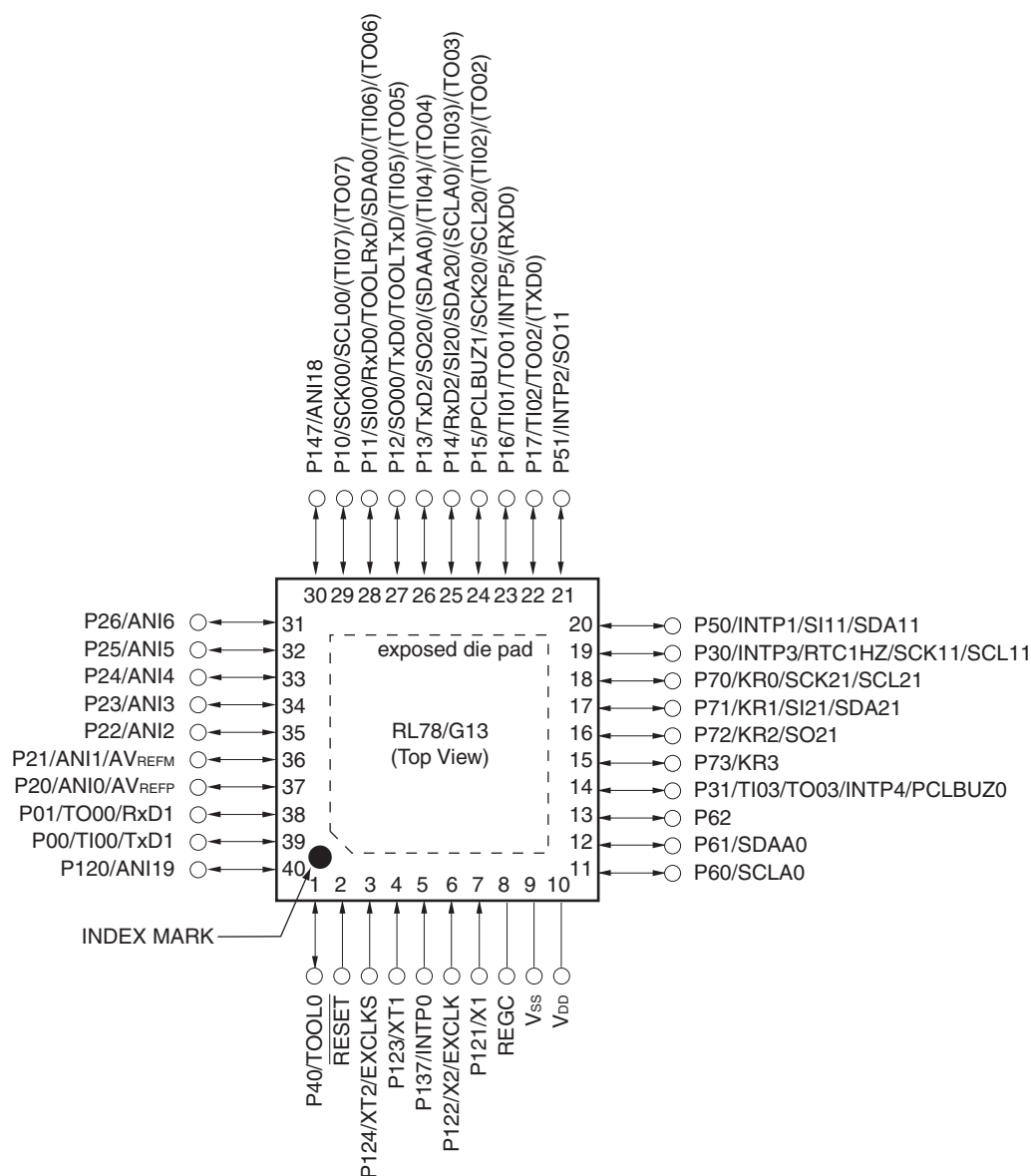
R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

1.3.7 40-pin products

- 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



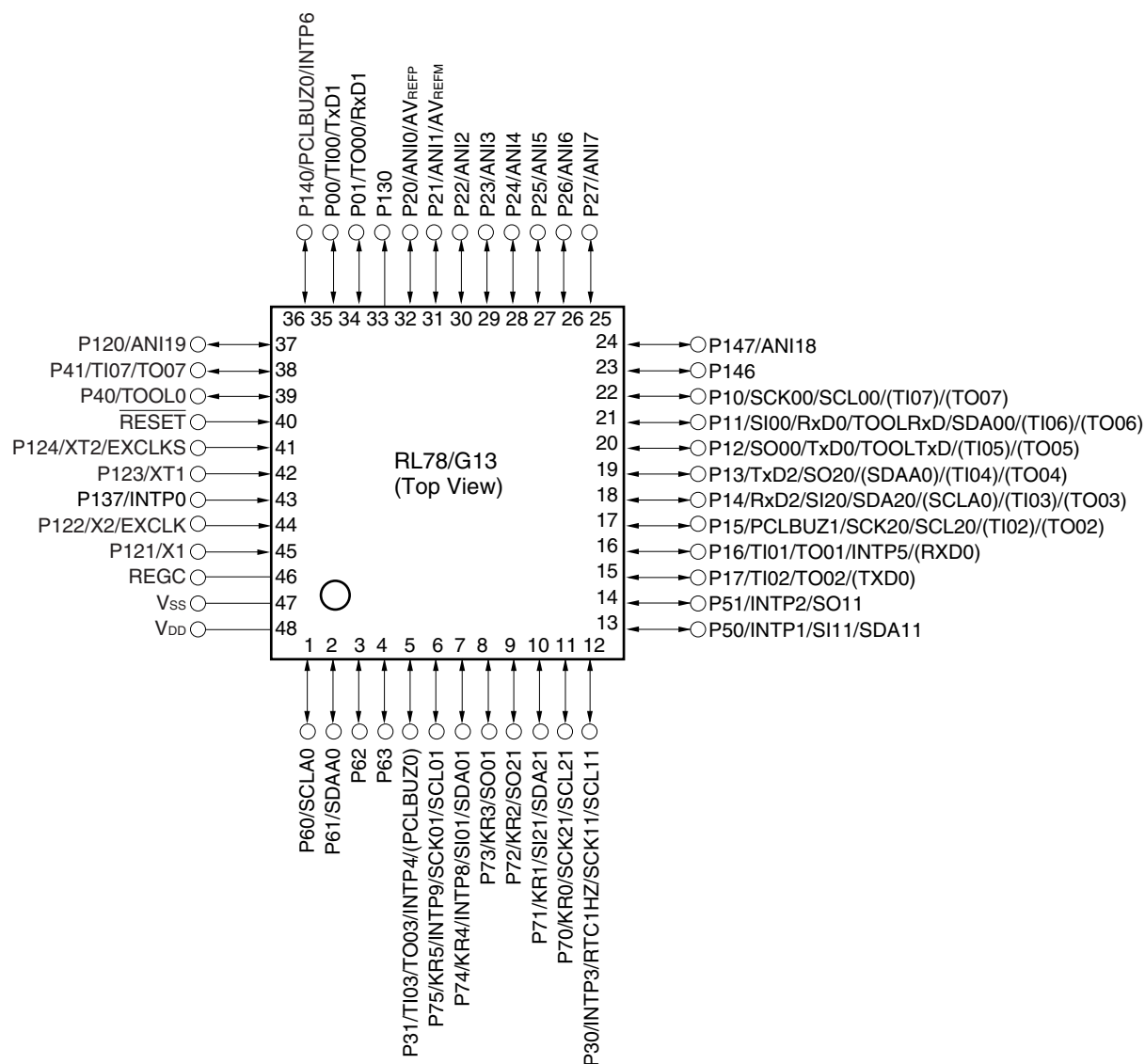
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
3. It is recommended to connect an exposed die pad to V_{SS}.

1.3.9 48-pin products

- 48-pin plastic LQFP (7 × 7 mm, 0.5 mm pitch)

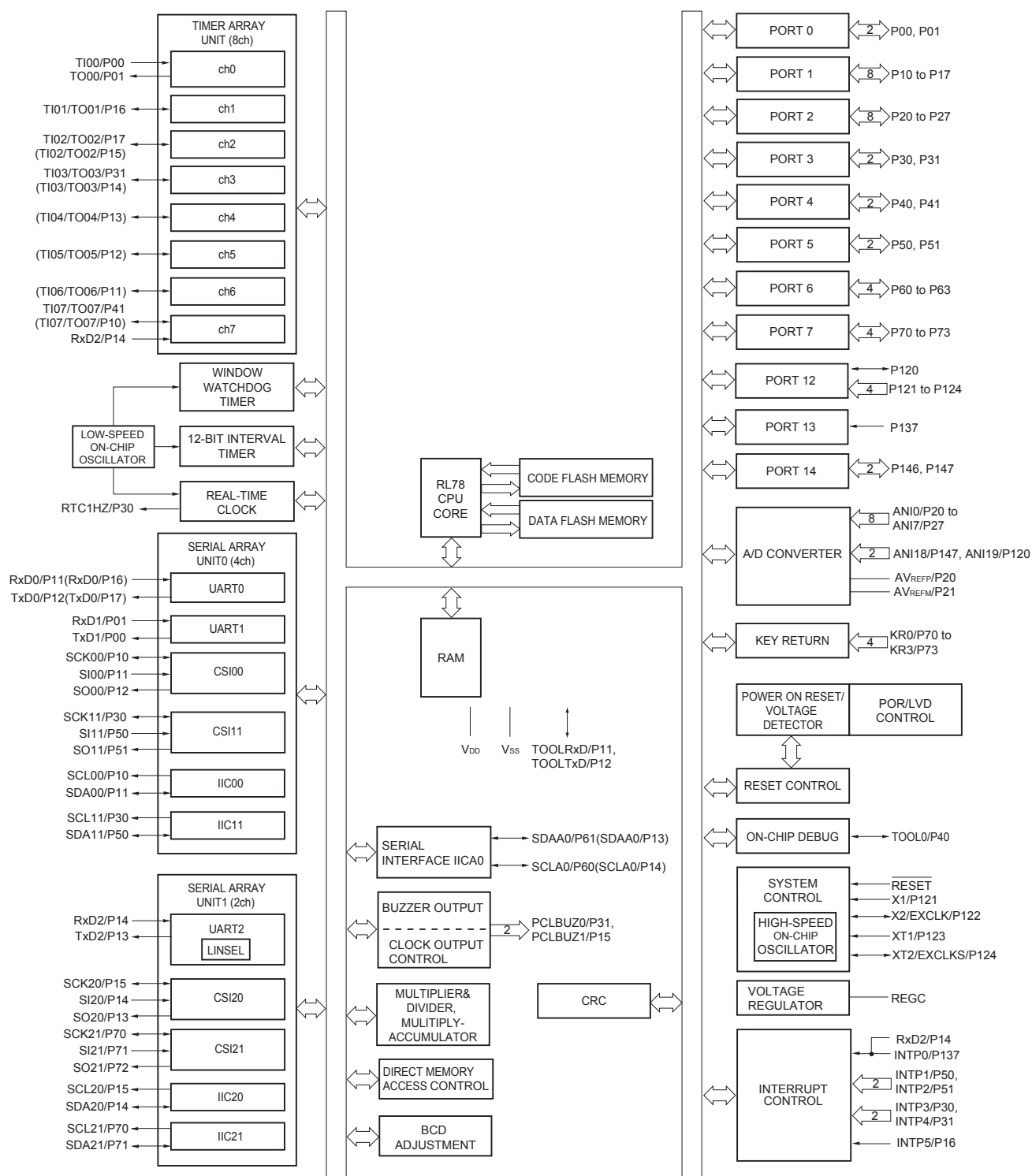


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.8 44-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		80-pin		100-pin		128-pin	
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx
Code flash memory (KB)		96 to 512		96 to 512		192 to 512	
Data flash memory (KB)		8	—	8	—	8	—
RAM (KB)		8 to 32 ^{Note 1}		8 to 32 ^{Note 1}		16 to 32 ^{Note 1}	
Address space		1 MB					
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)					
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)					
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz					
Low-speed on-chip oscillator		15 kHz (TYP.)					
General-purpose register		(8-bit register × 8) × 4 banks					
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)					
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)					
		30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)					
Instruction set		<ul style="list-style-type: none">• Data transfer (8/16 bits)• Adder and subtractor/logical operation (8/16 bits)• Multiplication (8 bits × 8 bits)• Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.					
I/O port	Total	74		92		120	
	CMOS I/O	64 (N-ch O.D. I/O [EVD _D withstand voltage]: 21)		82 (N-ch O.D. I/O [EVD _D withstand voltage]: 24)		110 (N-ch O.D. I/O [EVD _D withstand voltage]: 25)	
	CMOS input	5		5		5	
	CMOS output	1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)	4		4		4	
Timer	16-bit timer	12 channels		12 channels		16 channels	
	Watchdog timer	1 channel		1 channel		1 channel	
	Real-time clock (RTC)	1 channel		1 channel		1 channel	
	12-bit interval timer (IT)	1 channel		1 channel		1 channel	
	Timer output	12 channels (PWM outputs: 10 ^{Note 2})		12 channels (PWM outputs: 10 ^{Note 2})		16 channels (PWM outputs: 14 ^{Note 2})	
	RTC output	1 channel • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)					

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (3/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD0}	EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2	EV _{DD0}	V
			TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	2.0	EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	1.5	EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156	0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0	0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0	0.8	V
			TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0	0.5	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	0	0.32	V
	V _{IL3}	P20 to P27, P150 to P156	0		0.3V _{DD}	V
	V _{IL4}	P60 to P63	0		0.3EV _{DD0}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLKS, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes**
1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 3. When high-speed system clock and subsystem clock are stopped.
 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 32 MHz
 - $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 4 MHz

- Remarks**
1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH}: High-speed on-chip oscillator clock frequency
 3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

- Notes**
1. Total current flowing into V_{DD} , EV_{DD0} , and EV_{DD1} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} , and EV_{DD1} , or V_{SS} , EV_{SS0} , and EV_{SS1} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 32 MHz
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 4 MHz
 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH}: High-speed on-chip oscillator clock frequency
3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Transfer rate		Reception	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V			f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
					Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 4}			5.3		1.3	
			2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V			f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
					Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 4}			5.3		1.3	
			1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V			f _{MCK} /6 Notes 1 to 3		f _{MCK} /6 Notes 1, 2		f _{MCK} /6 Notes 1, 2	bps
					Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 4}			5.3		1.3	

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.**2.** Use it with EV_{DD0} ≥ V_b.**3.** The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps**4.** The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage**2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)**3.** f_{MCK}: Serial array unit operation clock frequency(Operation clock to be set by the CKS_{mn} bit of serial mode register mn (SMR_{mn}). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))**4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)
(1/3)(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK} 4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	300		1150		1150		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	500		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t _{KH1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 75		t _{KCY1} /2 – 75		t _{KCY1} /2 – 75		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 170		t _{KCY1} /2 – 170		t _{KCY1} /2 – 170		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 458		t _{KCY1} /2 – 458		t _{KCY1} /2 – 458		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 12		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 18		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns

Note Use it with EV_{DD0} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	t _{SU:DAT}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 135 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 135 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 100 pF, R _b = 5.5 kΩ	1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
Data hold time (transmission)	t _{HD:DAT}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	0	305	0	305	0	305	ns
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	0	355	0	355	0	355	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 100 pF, R _b = 5.5 kΩ	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.2. Use it with EV_{DD0} ≥ V_b.3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

2.8 Flash Memory Programming Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	1.8 V ≤ V _{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites <small>Notes 1, 2, 3</small>	C _{erwr}	Retained for 20 years T _A = 85°C	1,000			Times
Number of data flash rewrites <small>Notes 1, 2, 3</small>		Retained for 1 years T _A = 25°C		1,000,000		
		Retained for 5 years T _A = 85°C	100,000			
		Retained for 20 years T _A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

(3) Peripheral Functions (Common to all products)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
RTC operating current	I_{RTC} Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	I_{IT} Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	$f_{\text{IL}} = 15\text{ kHz}$			0.22		μA
A/D converter operating current	I_{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} = 5.0\text{ V}$		1.3	1.7	mA
			Low voltage mode, $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} = 3.0\text{ V}$		0.5	0.7	mA
A/D converter reference voltage current	I_{ADREF} Note 1				75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				75.0		μA
LVD operating current	I_{LVD} Notes 1, 7				0.08		μA
Self programming operating current	I_{FSP} Notes 1, 9				2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed ^{Note 10}		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} = 3.0\text{ V}$		1.20	2.04	mA
		CSI/UART operation			0.70	1.54	mA

Notes 1. Current flowing to the V_{DD} .

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either $I_{\text{DD}1}$ or $I_{\text{DD}2}$, and I_{RTC} , when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. $I_{\text{DD}2}$ subsystem clock operation includes the operational current of the real-time clock.4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either $I_{\text{DD}1}$ or $I_{\text{DD}2}$, and I_{IT} , when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 is the sum of $I_{\text{DD}1}$, $I_{\text{DD}2}$ or $I_{\text{DD}3}$ and I_{WDT} when the watchdog timer operates.

3.4 AC Characteristics

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{cy}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f _{SUB}) operation		2.4 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V			1.0		16.0	MHz
	f _{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V _{DD} < 2.7 V			30			ns
	t _{EXHS} , t _{EXLS}				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	t _{TIH} , t _{TIL}				1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV _{DD0} < 2.7 V				4	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV _{DD0} < 2.7 V				4	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0	2.4 V ≤ V _{DD} ≤ 5.5 V		1			μs
		INTP1 to INTP11	2.4 V ≤ EV _{DD0} ≤ 5.5 V		1			μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7	2.4 V ≤ EV _{DD0} ≤ 5.5 V		250			ns
RESET low-level width	t _{RSL}				10			μs

Note The following conditions are required for low voltage interface when $\text{EV}_{\text{DD}0} < \text{V}_{\text{DD}}$
 $2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 2.7\text{ V}$: MIN. 125 ns

Remark f_{MCK}: Timer array unit operation clock frequency
 (Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).
 m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate		Reception	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$		$f_{MCK}/12$ ^{Note 1}	bps
			V_b , $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$		2.6	Mbps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$			
			$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$		$f_{MCK}/12$ ^{Note 1}	bps
			V_b , $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$		2.6	Mbps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$			
			$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$		$f_{MCK}/12$ ^{Notes 1,2}	bps
			V_b , $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$		2.6	Mbps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$			

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2.** The following conditions are required for low voltage interface when $EV_{DD0} < V_{DD}$.
 $2.4\text{ V} \leq EV_{DD0} < 2.7\text{ V}$: MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Remarks 1. $V_b[V]$: Communication line voltage**2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)**3.** f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$ and $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

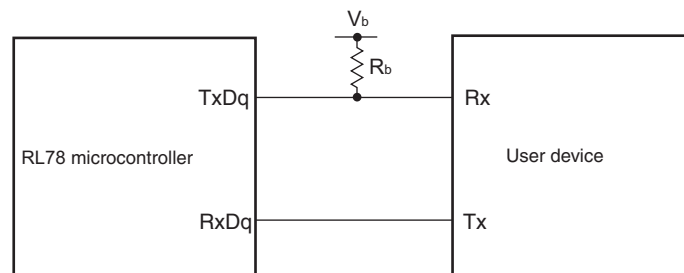
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

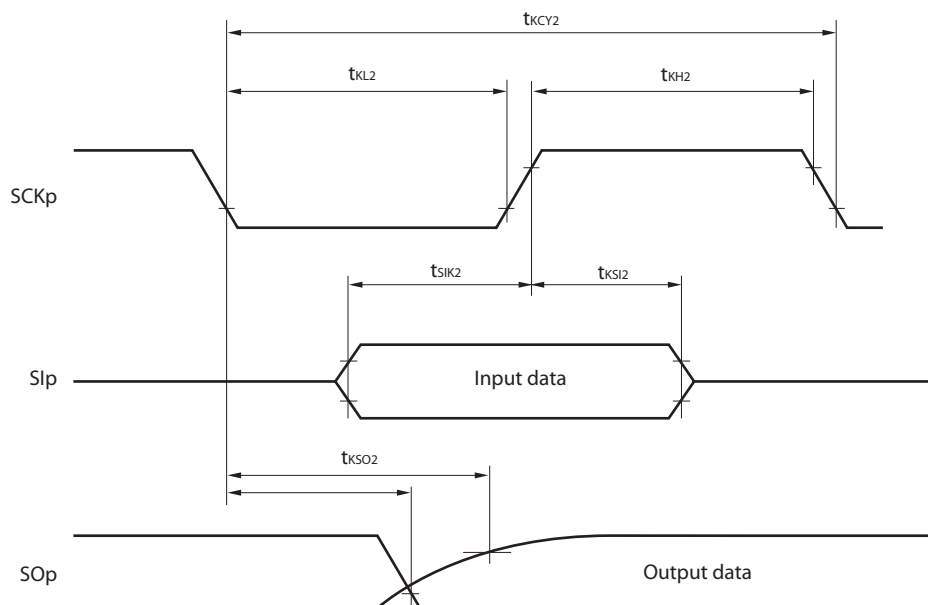
6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

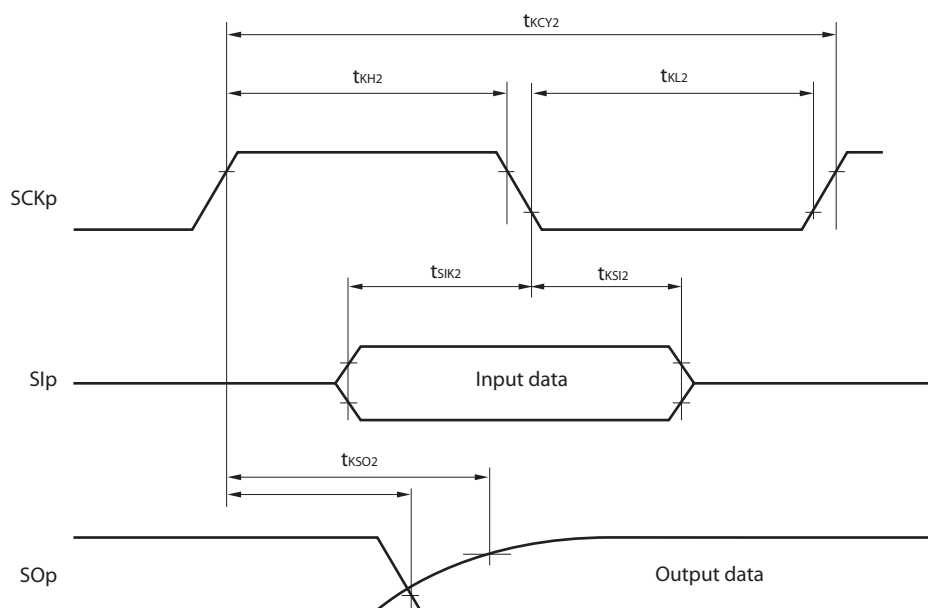
UART mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,
 n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
- 2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
 Use other CSI for communication at different potential.

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-) = AV_{REFM}
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI26	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1).		—

(1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

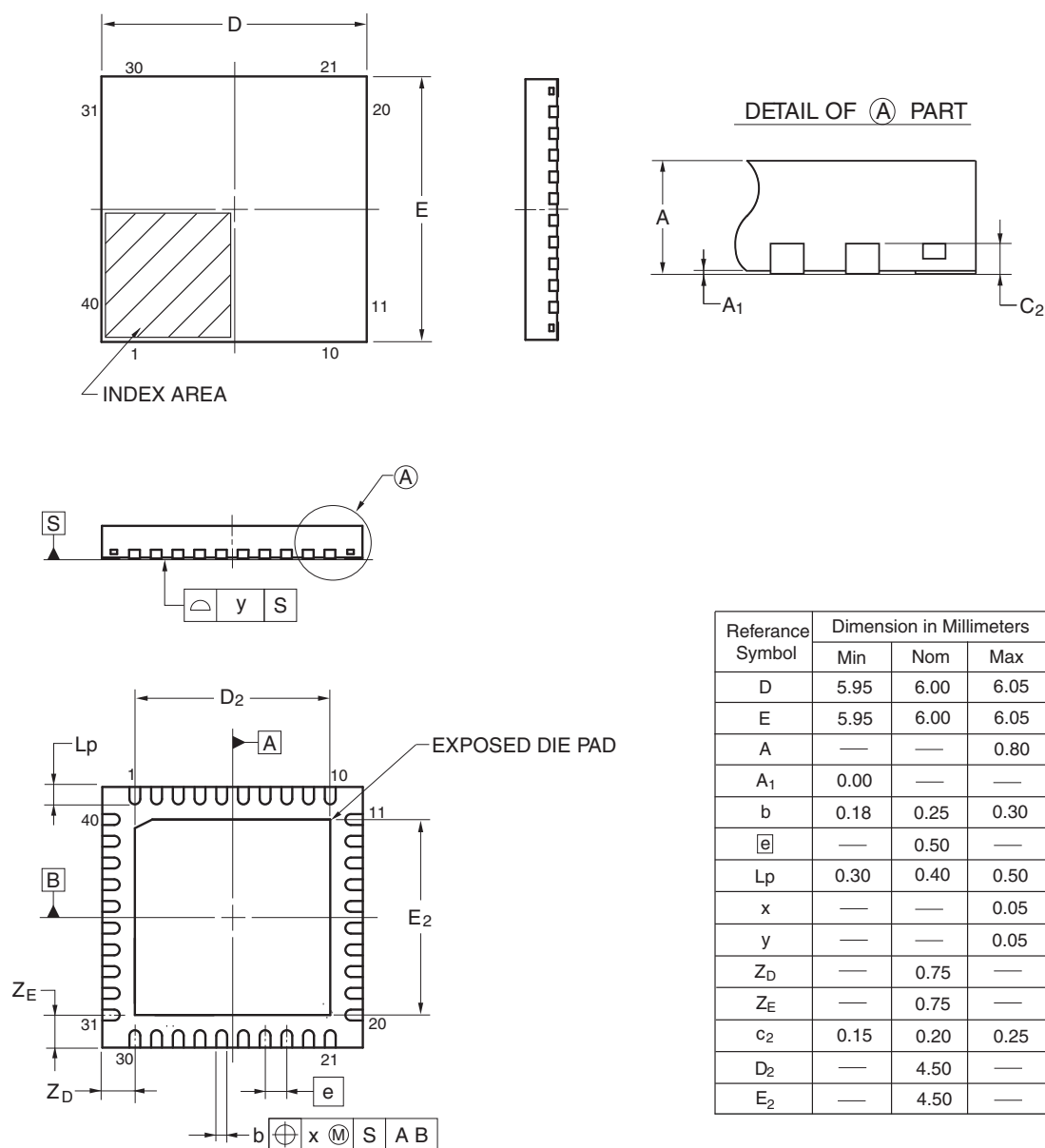
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$	1.2	± 3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.25	%FSR
Full-scale error ^{Notes 1, 2}	E_{FS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 2.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 1.5	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14	0		AV_{REFP}	V
		Internal reference voltage output ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)	V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)	V_{TMPS25} ^{Note 4}			V

(Notes are listed on the next page.)

4.7 40-pin Products

R5F100EAANA, R5F100ECANA, R5F100EDANA, R5F100EEANA, R5F100EFANA, R5F100EGANA, R5F100EHANA
 R5F101EAANA, R5F101ECANA, R5F101EDANA, R5F101EEANA, R5F101EFANA, R5F101EGANA, R5F101EHANA
 R5F100EADNA, R5F100ECDNA, R5F100EDDNA, R5F100EEDNA, R5F100EFDNA, R5F100EGDNA,
 R5F100EHDNA
 R5F101EADNA, R5F101ECDNA, R5F101EDDNA, R5F101EEDNA, R5F101EFDNA, R5F101EGDNA,
 R5F101EHDNA
 R5F100EAGNA, R5F100ECGNA, R5F100EDGNA, R5F100EEGNA, R5F100EFGNA, R5F100EGGNA,
 R5F100EHGNA

JEITA Package code	RENESAS code	Previous code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-5	0.09

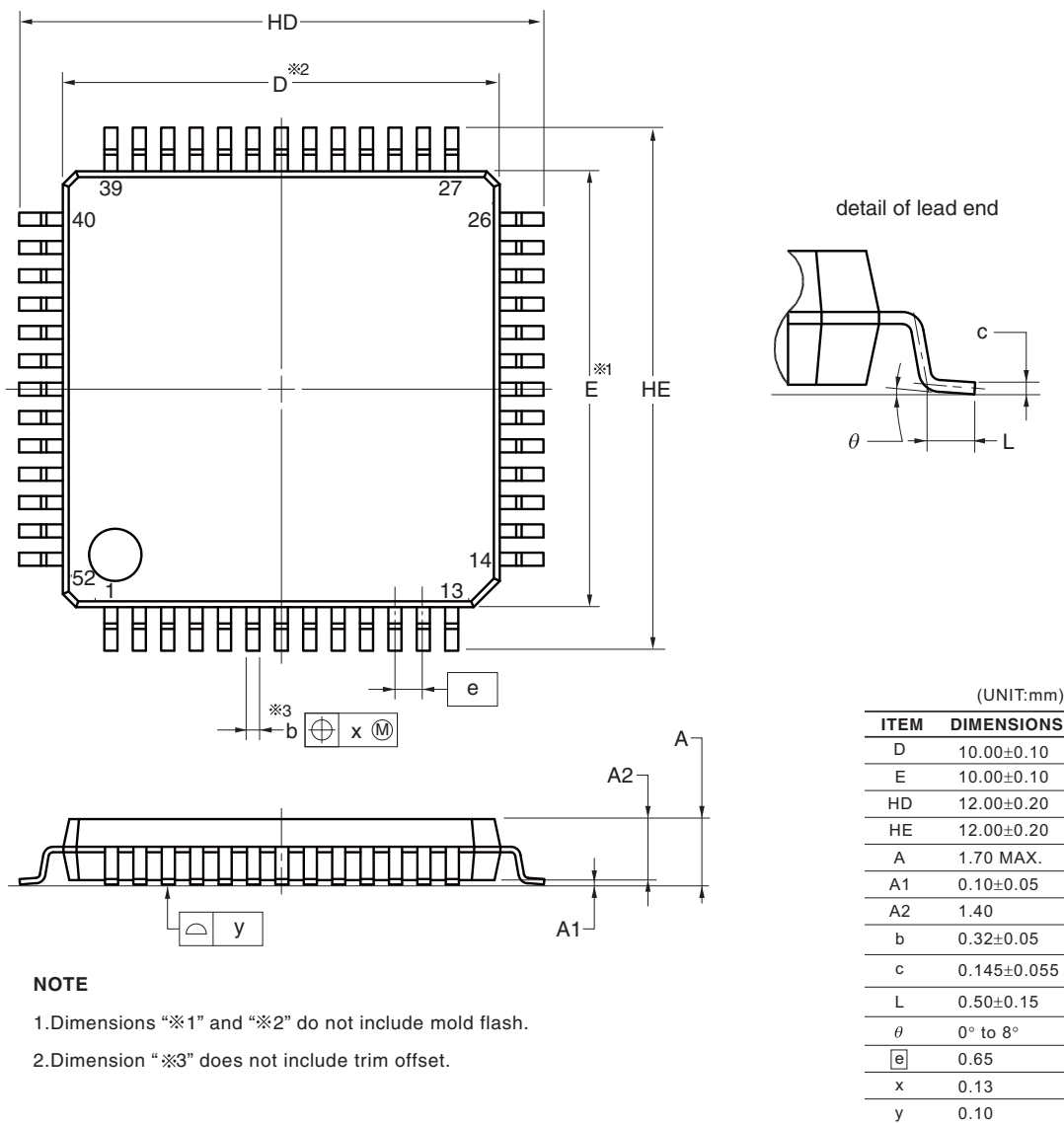


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4.10 52-pin Products

R5F100JCAFA, R5F100JDFA, R5F100JEFA, R5F100JFAFA, R5F100JGAFA, R5F100JHAFA, R5F100JJFA, R5F100JKFA, R5F100JLAFA
 R5F101JCAFA, R5F101JDFA, R5F101JEFA, R5F101JFAFA, R5F101JGAFA, R5F101JHAFA, R5F101JJFA, R5F101JKFA, R5F101JLAFA
 R5F100JCDA, R5F100JDDA, R5F100JEDA, R5F100JFDA, R5F100JGDA, R5F100JHDA, R5F100JJDA, R5F100JKDA, R5F100JLDA
 R5F101JCDA, R5F101JDDA, R5F101JEDA, R5F101JFDA, R5F101JGDA, R5F101JHDA, R5F101JJDA, R5F101JKDA, R5F101JLDA
 R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



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